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SD51

Schottky Barrier Rectifier Diode

Features

- Fast Switching
- Low forward voltage drop, V_F
- Guard ring protection
- High surge capacity
- High efficiency, low power loss

Electrical Ratings ($T_c = 25^{\circ}C$, unless otherwise noted)					
Parameter	Symbol	Values	Units		
Repetitive peak reverse voltage	V _{RRM}	45	V		
DC blocking voltage	V_{DC}	40			
Non-repetitive peak reverse voltage	V _{RSM}	54	V		
Average rectified forward current $(T_c = 85^{\circ}C)$	I _{F(AV)}	60	А		
Non-repetitive peak surge current (surge applied at rated load conditions, halfwave, single phase, 60 Hz	I _{FSM}	600	A		



DO-203AB (DO-5)

Maximum Ratings ($T_c = 25^{\circ}C$, unless otherwise noted)						
Parameter	Test Conditions	Symbol	Values	Units		
Maximum instantaneous forward voltage	I _F = 30 A	V _F	0.58	V		
	I _F = 60 A		0.66	V		
	I _F = 120 A		0.86	V		
Maximum instantaneous reverse current at rated DC voltage	$T_{c} = 25^{0}C$	- I _R	50	mA		
	$T_{C} = 125^{0}C$		125	mA		

Thermal & Mechanical Specifications ($T_E = 25^{\circ}C$, unless otherwise noted)					
Parameters	Symbol	Values	Units		
Maximum thermal resistance, junction to case	R _{th(JC)}	1.0	⁰ C/W		
Operating junction temperature range	TJ	-65 to +150	⁰ C		
Storage temperature	T _{stg}	-65 to +150	⁰ C		
Mounting torque (non-lubricated threads)		15	in-lb		
Approximate allowable weight	W	45.6	g		

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ALL DIMENSIONS IN MM